L Number	Hits	Search Text	DB	Time stamp
1	8	("111" adj plane adj substrate) with (recess or hollow or groove or (cut adj out) or hole or via)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:02
2	0	("111" adj plane) with (hollow adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:02
3	0	("111" adj plane) with (hollow near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:02
4	3	("111" adj plane) with (hollow with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:44
5	0	(soi adj (layer or film)) with (supporting adj substrate) with (crystal adj direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:45
6	1	(soi adj (layer or film)) with (substrate) with (crystal adj direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:46
7	3	(soi) with (substrate) with (crystal adj direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:36
8	0	(silicon adj "on" adj insulator) with (substrate) with (crystal adj direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:51
9	0	(silicon adj "on" adj insulator) with (substrate) with (direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:51
10	299	(soi) with (substrate) with (direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:52
11	8	(soi) with (substrate) with (direction) with different	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:54
12	2	(soi) with (substrate) with (orientation) with different	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:54
13	37	(soi) with (substrate) with (crystal adj orientation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 15:56
14	141	crystal adj (direction or orientation) adj different	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:37

15	3	(crystal adj (direction or orientation) adj different) and (soi with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:40
16	21	(crystal adj (direction or orientation) adj different) and ((semiconductor adj (layer or film)) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:55
17	0	crystal adj direction adj soi adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:55
18	51	crystal adj direction adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:55
19	1	(crystal adj direction adj substrate) and soi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:09
20	0	contact adj plug adj extending adj through adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:11
21	5	contact adj plug adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:11
22	0	(soi or (semiconductor adj "on" adj insulator)) adj (contact adj plug)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:12
23	1	(soi or (semiconductor adj "on" adj insulator)) near (contact adj plug)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:13
24	32	(soi or (semiconductor adj "on" adj insulator)) with (contact adj plug)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:17
25	12	(soi or (semiconductor adj "on" adj insulator)) with (contact adj via)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:18
26	290	(soi or (semiconductor adj "on" adj insulator)) with (contact adj hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:27
27	19	(soi or (semiconductor adj "on" adj insulator)) with (contact adj opening)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:32
28	4	6229165.pn. and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:32

–	17	(soi or (semiconductor adj "on" adj insulator)) and ((hollow or recessed) adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 17:12
–	514	(soi or (semiconductor adj "on" adj insulator)) and ((hollow or recessed) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 10:48
–	40	(soi or (semiconductor adj "on" adj insulator)) and ((cut adj out) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 10:57
–	225	((soi or (semiconductor adj "on" adj insulator)) and ((via or hole or opening) adj substrate)) and 257/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 11:16
–	2071	257/347.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 15:17
–	205	257/348.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 15:21
–	417	257/349.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 15:29
–	930	257/350.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 15:40
–	536	257/351.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 15:50
–	380	257/352.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 15:54
–	280	257/353.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/26 15:58
–	285	257/354.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 09:21
–	1	6084284.pn. and soi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 09:26
–	1	6084284.pn. and (mechanical adj support adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 09:27

-	0	6084284.pn. and (silicon adj support adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 09:28
-	1	6084284.pn. and (thick adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 09:27
-	1	6084284.pn. and (support adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 09:28
-	1	6084284.pn. and (support)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 10:23
-	280	substrate and (four adj faces)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 10:24
-	48	substrate with (four adj faces)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 10:33
-	5	substrate with (four adj end adj faces)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 10:36
-	1188	substrate with ("111" adj plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 10:37
-	160	substrate with ("111" adj plane) with (recess or hollow or groove or (cut adj out) or hole or via)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 14:59